

L Number	Hits	Search Text	DB	Time stamp
2	46	(TEOS or "tetra ethyl ortho silicate") and implant\$5 and (boron or phosphorous) and (HF or Hydrofluoric) and (resist or photoresist) and (second adj opening)	USPAT; EPO; JPO; IBM_TDB	2002/11/04 07:53
3	773	(TEOS or "tetra ethyl ortho silicate") and implant\$5 and (boron or phosphorous) and (HF or Hydrofluoric) and (resist or photoresist) and (contact or via or opening)	USPAT; EPO; JPO; IBM_TDB	2002/11/04 08:15
4	618	((TEOS or "tetra ethyl ortho silicate") and implant\$5 and (boron or phosphorous) and (HF or Hydrofluoric) and (resist or photoresist) and (contact or via or opening)) and (HF or Hydrofluoric) and vapor	USPAT; EPO; JPO; IBM_TDB	2002/11/04 08:16
5	457	(((TEOS or "tetra ethyl ortho silicate") and implant\$5 and (boron or phosphorous) and (HF or Hydrofluoric) and (resist or photoresist) and (contact or via or opening)) and (HF or Hydrofluoric) and vapor) and 438/\$.ccls.	USPAT; EPO; JPO; IBM_TDB	2002/11/04 08:17
9	1076	(TEOS or "tetra ethyl ortho silicate") and implant\$5 and etch\$5 and (resist or photoresist) and (contact or via or opening) and stack\$2	USPAT; EPO; JPO; IBM_TDB	2002/11/04 09:55
10	342	((TEOS or "tetra ethyl ortho silicate") and implant\$5 and etch\$5 and (resist or photoresist) and (contact or via or opening) and stack\$2) and (HF or Hydrofluoric) and vapor	USPAT; EPO; JPO; IBM_TDB	2002/11/04 09:08
11	266	(((TEOS or "tetra ethyl ortho silicate") and implant\$5 and etch\$5 and (resist or photoresist) and (contact or via or opening) and stack\$2) and (HF or Hydrofluoric) and vapor) and 438/\$.ccls.	USPAT; EPO; JPO; IBM_TDB	2002/11/04 08:30
12	312	(TEOS or "tetra ethyl ortho silicate") and implant\$5 and (boron or phosphorous) and (HF or Hydrofluoric) and (resist or photoresist) and (contact or via or opening) and stack\$2	USPAT; EPO; JPO; IBM_TDB	2002/11/04 09:59
13	9760	dop\$2 same (dielectric or insulating) same etch\$5	USPAT; EPO; JPO; IBM_TDB	2002/11/04 09:06
14	2687	(dop\$2 same (dielectric or insulating) same etch\$5) and (contact or via or opening) and stack\$2	USPAT; EPO; JPO; IBM_TDB	2002/11/04 09:07
15	674	((dop\$2 same (dielectric or insulating) same etch\$5) and (contact or via or opening) and stack\$2) and (HF or Hydrofluoric) and vapor	USPAT; EPO; JPO; IBM_TDB	2002/11/04 09:09
16	13	(second adj opening) same stack\$2 same implant\$5	USPAT; EPO; JPO; IBM_TDB	2002/11/04 10:02
17	339	(second adj opening) and stack\$2 and implant\$5	USPAT; EPO; JPO; IBM_TDB	2002/11/04 10:04